

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

I_{F(AV)}	10 A
V_{RRM}	45 V
V_F	0.57 V

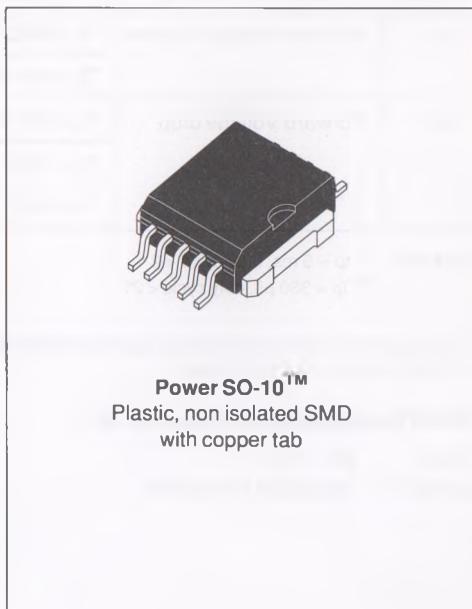
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH AVALANCHE CAPABILITY
- HIGH DISSIPATION MINIATURE PACKAGE
- SURFACE MOUNT TECHNOLOGY COMPATIBLE

DESCRIPTION

Dual schottky rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged in a high performance surface mount package PSO-10, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage		45	V
I _{F(RMS)}	RMS Forward Current (All pins connected)		27	A
I _{F(AV)}	Average Forward Current	T _c = 135 °C δ = 0.5	10	A
I _{FSM}	Surge Non Repetitive Forward Current (All pins connected)	t _p = 10 ms Sinusoidal	180	A
I _{RRM}	Repetitive Peak Reverse Current	t _p = 2 μs F = 1KHz	1	A
T _{stg} T _j	Storage and Junction Temperature Range		- 65 to + 150	°C
dV/dt	Critical Rate of Rise of Reverse Voltage		1000	V/μs

TM : PowerSO-10 is a trademark of SGS-THOMSON Microelectronics.

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{TH(j-c)}$	Junction to Case Thermal Resistance	2.2	°C/W

STATIC ELECTRICAL CHARACTERISTICS (Per diode)

Symbol	Tests Conditions	Tests Conditions		Min.	Typ.	Max.	Unit
I_R *	Reverse leakage Current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			100	μA
		$T_j = 125^\circ\text{C}$				15	mA
V_F **	Forward Voltage drop	$T_j = 125^\circ\text{C}$	$I_F = 20 \text{ A}$			0.72	V
		$T_j = 125^\circ\text{C}$	$I_F = 10 \text{ A}$			0.57	
		$T_j = 25^\circ\text{C}$	$I_F = 20 \text{ A}$			0.84	

Pulse test : * $t_p = 5 \text{ ms}$, duty cycle < 2 %** $t_p = 380 \mu\text{s}$, duty cycle < 2%

To evaluate the conduction losses use the following equation :

$$P = 0.42 \times I_{F(\text{AV})} + 0.015 I_F^2 (\text{RMS})$$

PIN OUT configuration in PowerSO-10 :

Anode = pin 1 to 5

Cathode = connected to base tab

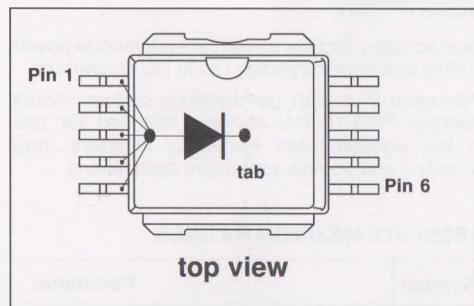


Fig. 1 : Average forward power dissipation versus average forward current.

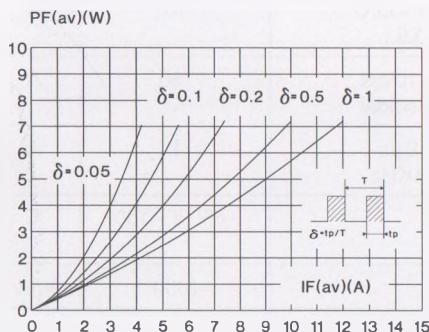


Fig. 2 : Average current versus ambient temperature. (duty cycle : 0.5)

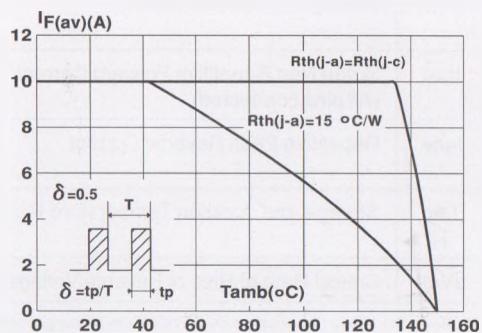


Fig. 3 : Non repetitive surge peak forward current versus overload duration. (Maximum values)

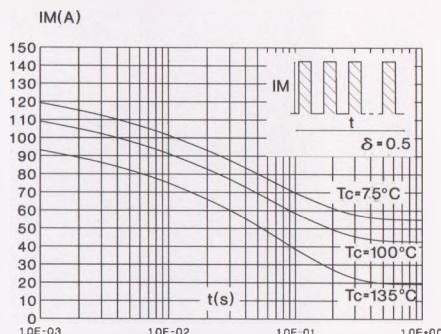


Fig. 5 : Reverse leakage current versus reverse voltage applied. (Typical values)

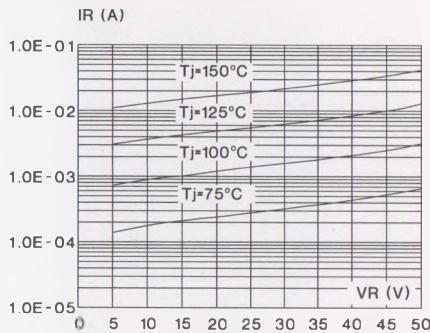


Fig. 7 : Forward voltage drop versus forward current. (Maximum values)

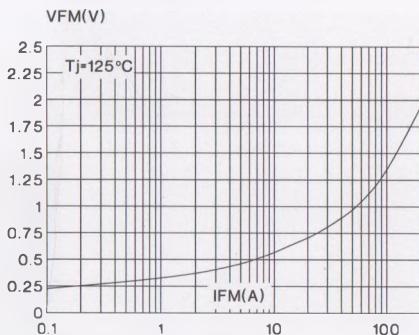


Fig. 4 : Relative variation of thermal transient impedance junction to case versus pulse duration.

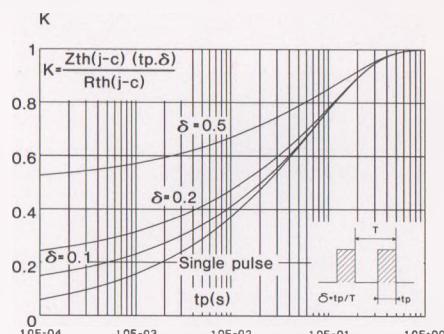


Fig. 6 : Junction capacitance versus reverse voltage applied. (Typical values)

